

Appl. No. 10/003,908
Amtd dated August 13, 2004
Reply to Office Action of May 19, 2004.

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8/23/04

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listings of Claims:

Claim 1: (currently amended) A method of operating a deposition process chamber, the method comprising:

- placing a substrate in said process chamber;
- depositing a film on said substrate, said depositing leaving a deposition residue on an interior surface of said chamber; and
- cleaning said deposition residue from said interior surface by creating a fluorine-containing plasma in said chamber, said fluorine-containing plasma leaving a fluorine-containing contaminant on said interior surface; and thereafter removing said fluorine-containing contaminant by
- supplying an oxygen-containing gas into the process chamber;
- supplying a hydrogen-containing gas into the process chamber, said hydrogen-containing gas being different from said oxygen-containing gas;
- producing a plasma comprising of a mixture of the oxygen-containing gas and the hydrogen-containing gas, thereby exothermically producing H₂O;
- causing so that the plasma to react reacts with the fluorine-containing contaminant to form a fluorine-containing material; and
- removing the fluorine-containing material from the process chamber.

Claim 2: (previously presented) The method of claim 1, wherein the hydrogen-containing gas is selected from a group consisting of NH₃ and H₂.

Claim 3: (previously presented) The method of claim 1, wherein the oxygen-containing gas is selected from a group consisting of N₂O, O₂ and air.

Claim 4: (canceled)

Claim 5: (previously presented) The method of claim 1, wherein producing the plasma produces an ion flux to an interior surface of the process chamber, so that the ion

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